

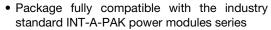
Vishay Semiconductors

Three Phase AC Switch (Power Modules), 50 A to 100 A



PRODUCT SUMMARY							
I _O	50 A to 100 A						
V _{RRM}	800 V to 1600 V						
Package	MT-K						
Circuit	Three phase AC switch						

FEATURES





- High thermal conductivity package, electrically insulated case
- Outstanding number of power encapsulated components
- Excellent power volume ratio
- 4000 V_{RMS} isolating voltage
- UL E78996 approved
- · Designed and qualified for industrial level
- Material categorization: For definitions of compliance please see <u>www.vishav.com/doc?99912</u>

DESCRIPTION

A range of extremely compact, encapsulated three phase AC switches offering efficient and reliable operation. They are intended for use in general purpose and heavy duty applications as control motor starter.

MAJOR RAT	INGS AND CHARACTERIST	rics					
SYMBOL	CHARACTERISTICS	VALUES 54MT.K	VALUES 94MT.K	VALUES 104MT.K	UNITS		
1		50	90	100	Α		
IO	T _C	80	80	80	°C		
1	50 Hz	390	950	1130	^		
IFSM	60 Hz	410	1000	1180	A		
I ² t	50 Hz	770	4525	6380	• 2		
1-1	60 Hz	700	4130	5830	A ² s		
I ² √t		7700 45250 63800			A²√s		
V_{RRM}	Range		V				
T _{Stg}	Range	-40 to 125 °C					
TJ	Range		-40 to 125		°C		

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS									
TYPE NUMBER	VOLTAGE CODE	V _{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE V	V _{DRM} , MAXIMUM REPETITIVE PEAK OFF-STATE VOLTAGE, GATE OPEN CIRCUIT V	I _{RRM} /I _{DRM} , MAXIMUM AT T _J = 125 °C mA				
	80	800	900	800					
	100	1000	1100	1000					
VS-54MTK	120	1200	1300	1200	20 (1)				
	140	1400	1500	1400					
	160	1600	1700	1600					
	80	800	900	800					
	100	1000	1100	1000					
VS-94/104MTK	120	1200	1300	1200	40 ⁽¹⁾				
	140	1400	1500	1400	1				
	160	1600	1700	1600					

Note

(1) For single AC switch



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FORWARD CONDUCTION								
PARAMETER	SYMBOL		TEST CONDITION	ONS	VALUES 54MT.K	VALUES 94MT.K	VALUES 104MT.K	UNITS
Maximum I _{RMS} output current) <u> </u>	For all condu	action angle		50	90	100	Α
at case temperature	10	1 of all corlac	ction angle		80	80	80	°C
		t = 10 ms	No voltage		390	950	1130	
Maximum peak, one-cycle forward, non-repetitive	l	t = 8.3 ms	reapplied		410	1000	1180	Α
on state surge current	I _{TSM}	t = 10 ms	100 % V _{RRM}		330	800	950	^
-		t = 8.3 ms	reapplied	Initial $T_J = T_J$	345	840	1000	
		t = 10 ms	No voltage	maximum	770	4525	6380	
Maximum I2t for fusing	I ² t	t = 8.3 ms	reapplied		700	4130	5830	A ² s
Maximum i-t for fusing	1-1	t = 10 ms	100 % V _{RRM}		540	3200	4510	
	,	t = 8.3 ms	reapplied		500	2920	4120	
Maximum I ² √t for fusing	I ² √t	t = 0.1 ms to	10 ms, no volta	ge reapplied	7700	45 250	63 800	A²√s
Low level value of threshold voltage	V _{T(TO)1}	(16.7 % x π >	$I_{T(AV)} < I < \pi \times I_{T}$	1.16	0.99	0.99	V	
High level value of threshold voltage	V _{T(TO)2}	$(I > \pi \times I_{T(AV)})$, T _J maximum		1.44	1.19	1.15	V
Low level value on-state slope resistance	r _{t1}	16.7 % x π x	$I_{T(AV)} < I < \pi \times I_{T(AV)}$	_(AV)), T _J maximum	12.54	4.16	3.90	mΩ
High level value on-state slope resistance	r _{t2}	$(I > \pi \times I_{T(AV)})$, T _J maximum	11.00	3.56	3.48	11122	
Maximum on-state voltage drop	V _{TM}	I_{pk} = 150 A, T_J = 25 °C t_p = 400 μs single junction			2.68	1.55	1.53	V
Maximum non-repetitive rate of rise of turned on current	dl/dt	$I_{J} = 25$ °C, from 0.67 V_{DRM} , $I_{TM} = \pi \times I_{T(AV)}$, $I_{g} = 500$ mA, $t_{r} < 0.5$ µs, $t_{p} > 6$ µs				150		A/µs
Maximum holding current	I _H		T _J = 25 °C, anode supply = 6 V, resistive load, grate open circuit			200		mA
Maximum latching current	ΙL	$T_J = 25 ^{\circ}C$, a	node supply = 6	V, resistive load		400		

BLOCKING								
PARAMETER	SYMBOL	TEST CONDITIONS	54MT.K	94MT.K	104MT.K	UNITS		
RMS isolation voltage	V _{INS}	T_J = 25 °C all terminal shorted f = 50 Hz, t = 1 s				V		
Maximum critical rate of rise of off-state voltage	dV/dt (1)	dV/dt (1) T _J = T _J maximum, linear to 0.67 V _{DRM} , gate open circuit 500			V/µs			

Note

 $^{(1)}$ Available with dV/dt = 1000 V/ μs , to complete code add S90 i. e. 104MT160KBS90

TRIGGERING									
PARAMETER	SYMBOL		TEST CONDITIONS	54MT.K	94MT.K	104MT.K	UNITS		
Maximum peak gate power	P_{GM}				10		W		
Maximum average gate power	P _{G(AV)}				2.5		l vv		
Maximum peak gate current	I _{GM}	$T_J = T_J \text{ maxir}$	num		2.5		Α		
Maximum peak negative gate voltage	- V _{GT}				10				
		$T_J = 40 ^{\circ}\text{C}$	T _J = 40 °C		4.0		V		
Maximum required DC gate voltage to trigger	V_{GT}	T _J = 25 °C			2.5				
voltage to trigger		$T_J = 125 ^{\circ}\text{C}$ Anode supply = 6 V, resistive		$T_J = 125 ^{\circ}\text{C}$ Anode supply = 6 V, resistive					
		T _J = -40 °C			270				
Maximum required DC gate current to trigger	I _{GT}	T _J = 25 °C			150		mA		
current to trigger		T _J = 125 °C			80				
Maximum gate voltage that will not trigger	V _{GD}	T – T movir	num rated // applied		0.25		V		
Maximum gate current that will not trigger	I _{GD}	ij=ijmaxii	num, rated V _{DRM} applied		6		mA		



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THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER	SYMBOL	TEST CONDITIONS	54MT.K	94MT.K	104MT.K	UNITS			
Maximum junction operating and storage temperature range	T _J , T _{Stg}			-40 to 125		°C			
		DC operation per single AC switch	0.52	0.39	0.34				
Maximum thermal resistance,	R _{thJC}	DC operation per junction	1.05	0.77	0.69				
junction to case	TthJC	180 °C sine cond. angle per single AC switch	0.56	0.40	0.36	K/W			
		180 °C sine cond. angle per junction	1.12	0.80	0.72	1011			
Maximum thermal resistance, case to heatsink	R _{thCS}	Per module Mounting surface smooth, flat and grased	0.03						
Mounting to heatsink		A mounting compound is recommended and 4 to 6			Nm				
torque ± 100 % to terminal		the torque should be rechecked after a period of 3 hours to allow for the spread of		3 to 4		INIII			
Approximate weight		the compound. Lubricated threads.				g			

△R CONDUCTION PER JUNCTION											
DEVICES		SINUSOIDAL CONDUCTION AT T _J MAXIMUM					N RECTANGULAR CONDUCTION AT T _J MAXIMUM			N	UNITS
	180°	120°	90°	60°	30°	180°	120°	90°	60°	30°	
54MT.K	0.072	0.085	0.108	0.152	0.233	0.055	0.091	0.117	0.157	0.236	
94MT.K	0.033	0.039	0.051	0.069	0.099	0.027	0.044	0.055	0.071	0.100	K/W
104MT.K	0.027	0.033	0.042	0.057	0.081	0.023	0.037	0.046	0.059	0.082	

Note

Table shows the increment of thermal resistance R_{thJC} when devices operate at different conduction angles than DC

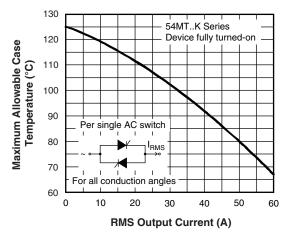


Fig. 1 - Current Ratings Characteristic

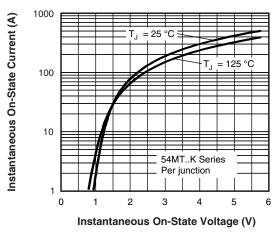
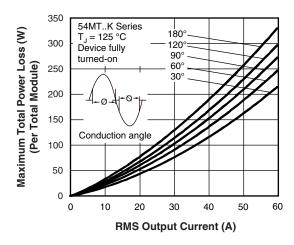


Fig. 2 - Forward Voltage Drop Characteristics



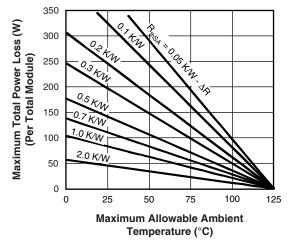


Fig. 3 - Total Power Loss Characteristics

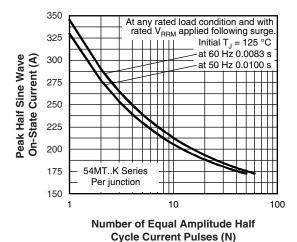


Fig. 4 - Maximum Non-Repetitive Surge Current

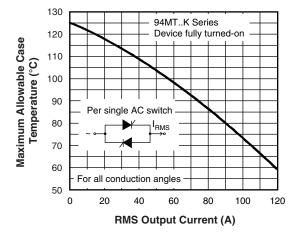


Fig. 6 - Current Ratings Characteristic

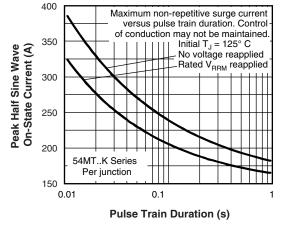


Fig. 5 - Maximum Non-Repetitive Surge Current

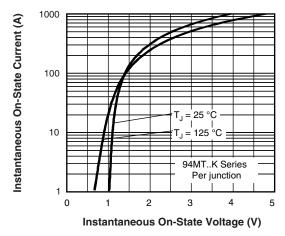
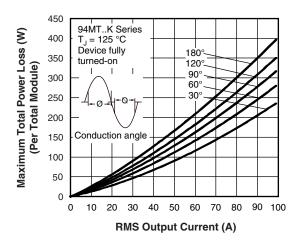


Fig. 7 - Forward Voltage Drop Characteristics



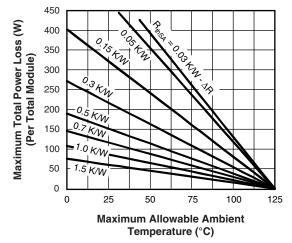


Fig. 8 - Total Power Loss Characteristics

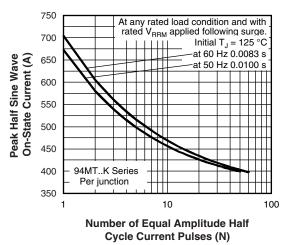


Fig. 9 - Maximum Non-Repetitive Surge Current

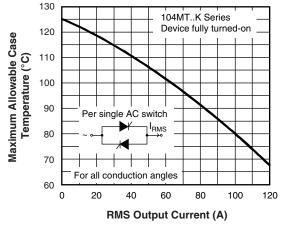


Fig. 11 - Current Ratings Characteristic

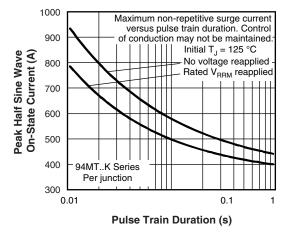


Fig. 10 - Maximum Non-Repetitive Surge Current

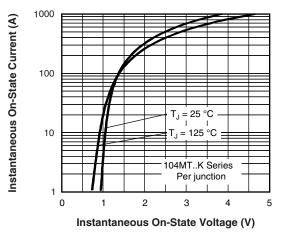
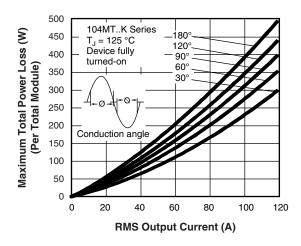


Fig. 12 - Forward Voltage Drop Characteristics



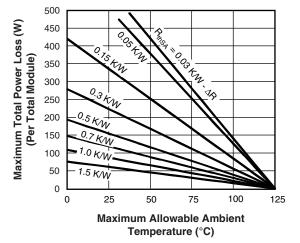


Fig. 13 - Total Power Loss Characteristics

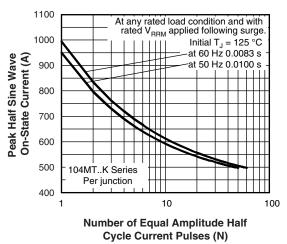


Fig. 14 - Maximum Non-Repetitive Surge Current

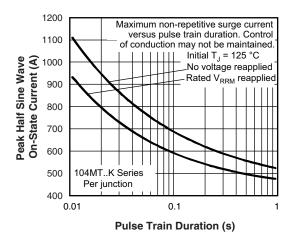


Fig. 15 - Maximum Non-Repetitive Surge Current

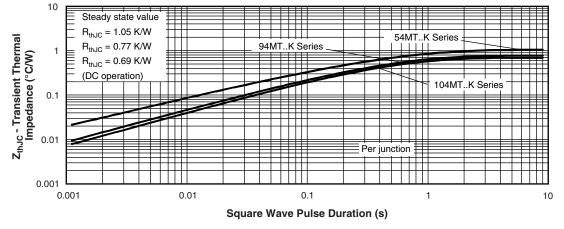


Fig. 16 - Thermal Impedance Z_{thJC} Characteristics

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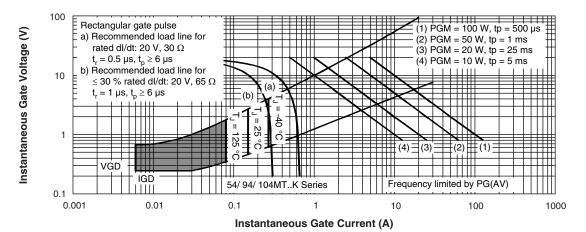
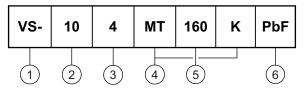


Fig. 17 - Gate Characteristics

ORDERING INFORMATION TABLE





1 - Vishay Semiconductors product

- Current rating code: 5 = 50 A (average)

9 = 90 A (average) 10 = 100 A (average)

3 - AC switch

4 - Essential part number

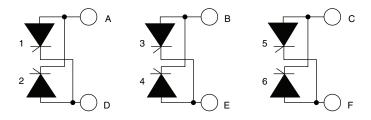
Voltage code x 10 = V_{RRM} (see Voltage Ratings table)

6 - PbF = Lead (Pb)-free

Note

• To order the optional hardware go to www.vishay.com/doc?95172

CIRCUIT CONFIGURATION

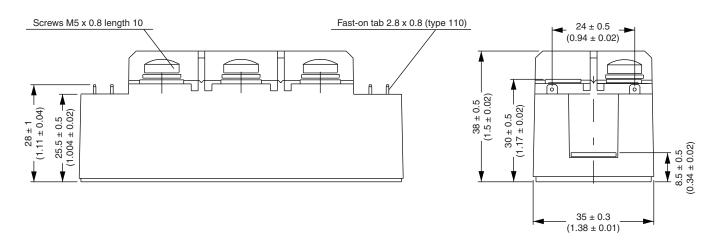


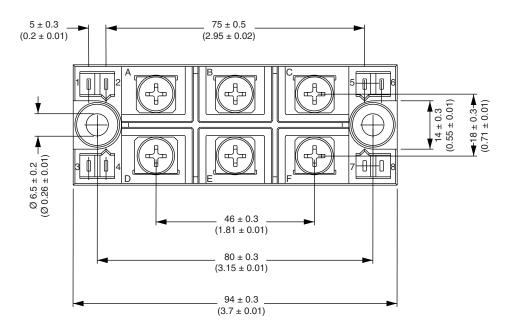
LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95004				



MTK (with and without optional barrier)

DIMENSIONS WITH OPTIONAL BARRIERS in millimeters (inches)

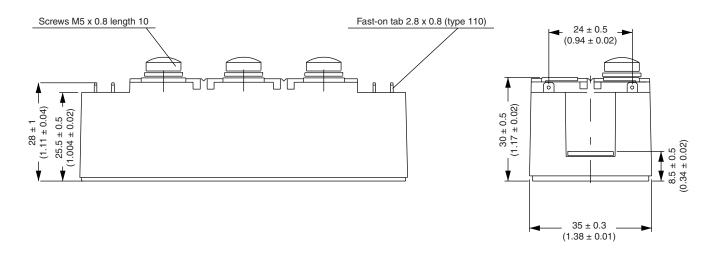


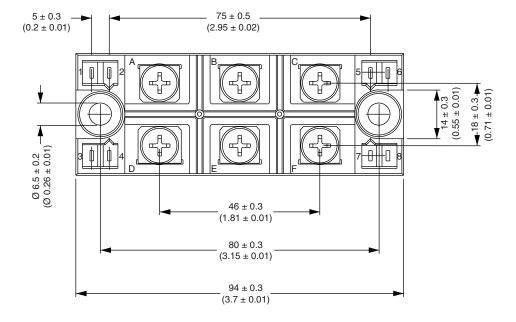


Vishay Semiconductors MTK (with and without optional barrier)



DIMENSIONS WITHOUT OPTIONAL BARRIERS in millimeters (inches)







Legal Disclaimer Notice

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Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

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Revision: 02-Oct-12 Document Number: 91000